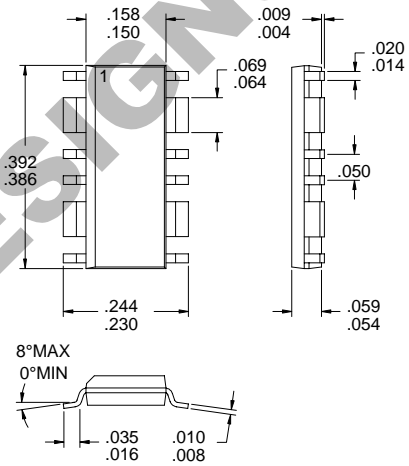


Typical Applications

- 4.8V DCS1800/1900 Handsets
- Commercial and Consumer Systems
- 3V DECT Handsets and Base Stations
- Portable Battery Powered Equipment

Product Description

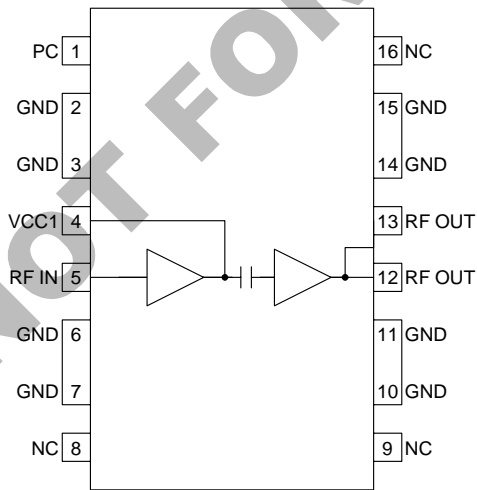
The RF2145 is a high power, high efficiency amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in a 4-cell DCS1800 or DCS1900 handset. The device is packaged in a 16-lead plastic package with wide ground leads, and is self-contained with the exception of the output matching network and power supply feed line. Only a single positive voltage is required to operate with full power and efficiency, and on-board power control and power-down functions are provided.



Package Style: SOP-16 QBW1

Optimum Technology Matching® Applied

- Si BJT GaAs HBT GaAs MESFET
 Si Bi-CMOS SiGe HBT Si CMOS



Functional Block Diagram

Features

- Single 4.8V Power Supply
- +32dBm Output Power
- 28dB Small Signal Gain
- 55% Power Added Efficiency
- Power Control
- 1700MHz to 1900MHz Frequency Range

Ordering Information

- RF2145 DCS1800/1900 Power Amplifier
 RF2145 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

RF2145

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +7.5	V _{DC}
Power Control Voltage (V _{PC})	-0.5 to +3.0	V
DC Supply Current	675	mA
Input RF Power	+12	dBm
Output Load VSWR	5:1	
Ambient Operating Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



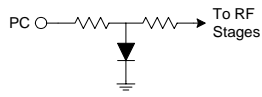
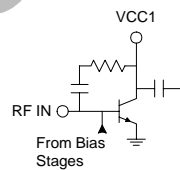
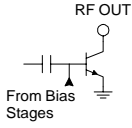
Caution! ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

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POWER AMPLIFIERS

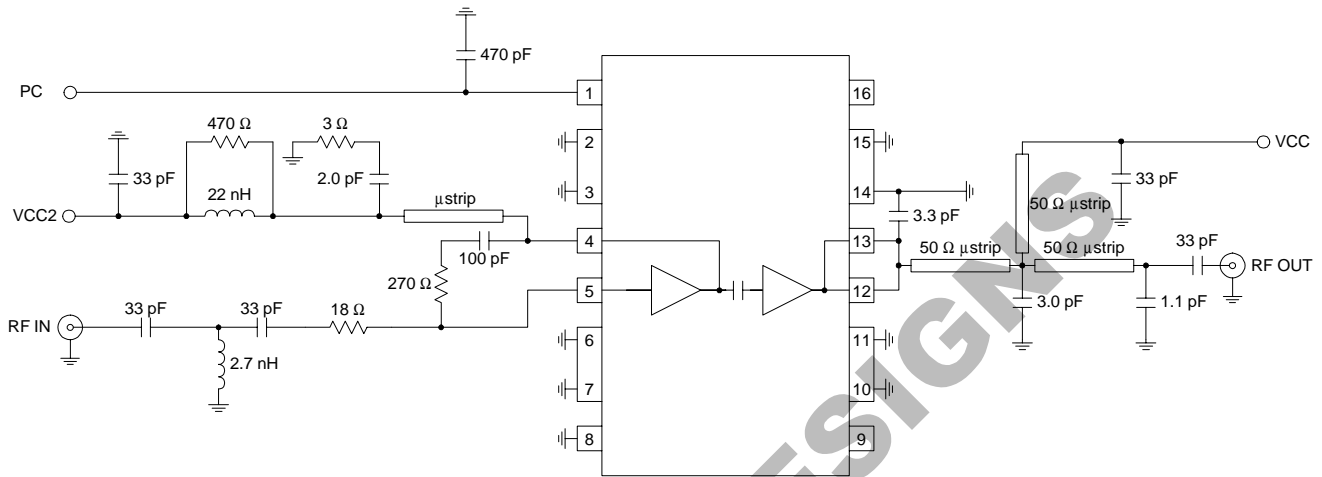
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					T=25 °C, V _{CC} =4.8V, V _{PC} =2.5V, P _{IN} =+8dBm, Freq=1750MHz
Operating Frequency Range		1710 to 1785 1850 to 1910		MHz	
Usable Frequency Range		1700 to 1990		MHz	
Maximum Output Power		+32		dBm	1/8 Duty cycle with 600µs pulse width
Total Efficiency		55		%	At maximum output power
Input Power for Max Output		+8		dBm	
Input Intermodulation Distortion		-57		dBc	Input signal consists of F ₁ at 1785MHz at +8dBm, F ₂ at 1765MHz at -42dBm. Output power at F ₁ is set to +32.5dBm. Specified power level at 1805MHz relative to F ₁ . This refers to the amount of TX band noise which converts into the receive band.
		-48		dBc	Input signal consists of F ₁ at 1785MHz at +8dBm, F ₂ at 1765MHz at -32dBm. Output power at F ₁ is set to +32.5dBm. Specified power level at 1805MHz relative to F ₁ . This refers to the amount of TX band noise which converts into the receive band.
Output Noise Power in Receive Band		-137		dBm/Hz	Any gain setting
Isolation		-25		dBm	In "OFF" state, P _{IN} =+8dBm
Second Harmonic		-48		dBc	
Third Harmonic		<-60		dBc	
Input Impedance		50		Ω	
Input VSWR			3.8:1		Worst-case across the band. Using evaluation board; can be different with other layouts
Output Load VSWR	3:1				Spurious<-60dBc
Power Control					
Power Control "ON"		2.5	3.0	V	Threshold voltage
Power Control "OFF"	0.2	0.5		V	Threshold voltage
Current into PC Input		15		mA	In "ON" state
			10	µA	In "OFF" state
Power Control Range	45			dB	
Turn On/Off Time			100	ns	
Power Supply					
Power Supply Voltage		4.8		V	Specifications
	2.7		6.5	V	Operating limits
Power Supply Current		550		mA	DC Current at maximum output power
			10	µA	V _{PC} =0.5V

Pin	Function	Description	Interface Schematic
1	PC	Power control pin. This also provides power down when V_{PC} is less than +0.5V. Full power is achieved at 2.5V, and >45dB of gain control is obtainable over the full range. Approximately 15mA current is drawn into this pin at full power.	
2	GND	Ground connection. This pin should be connected to the ground plane through a short path and may be combined with the ground plane from Pins 3, 6, 7, 10, 11, 14, and 15. All four of these wide leads are tied together internally to provide a low-inductance and low thermal resistance path to external ground. Ground vias should be placed as close as possible to each ground lead.	
3	GND	Same as pin 2.	
4	VCC1	Power supply pin for the first stage. Also provides tuning for interstage match.	
5	RF IN	RF input. This input is DC coupled, so an external blocking capacitor is required if this pin is connected to a DC path.	See pin 4 schematic.
6	GND	Same as pin 2.	
7	GND	Same as pin 2.	
8	NC	No connection.	
9	NC	No connection.	
10	GND	Same as pin 2.	
11	GND	Same as pin 2.	
12	RF OUT	RF output pin. Bias is also fed to the final stage through this wide lead. External matching is most easily achieved with a series transmission line and shunt capacitors, as shown in the application schematic.	
13	RF OUT	Same as pin 12.	
14	GND	Same as pin 2.	
15	GND	Same as pin 2.	
16	NC	No connection.	

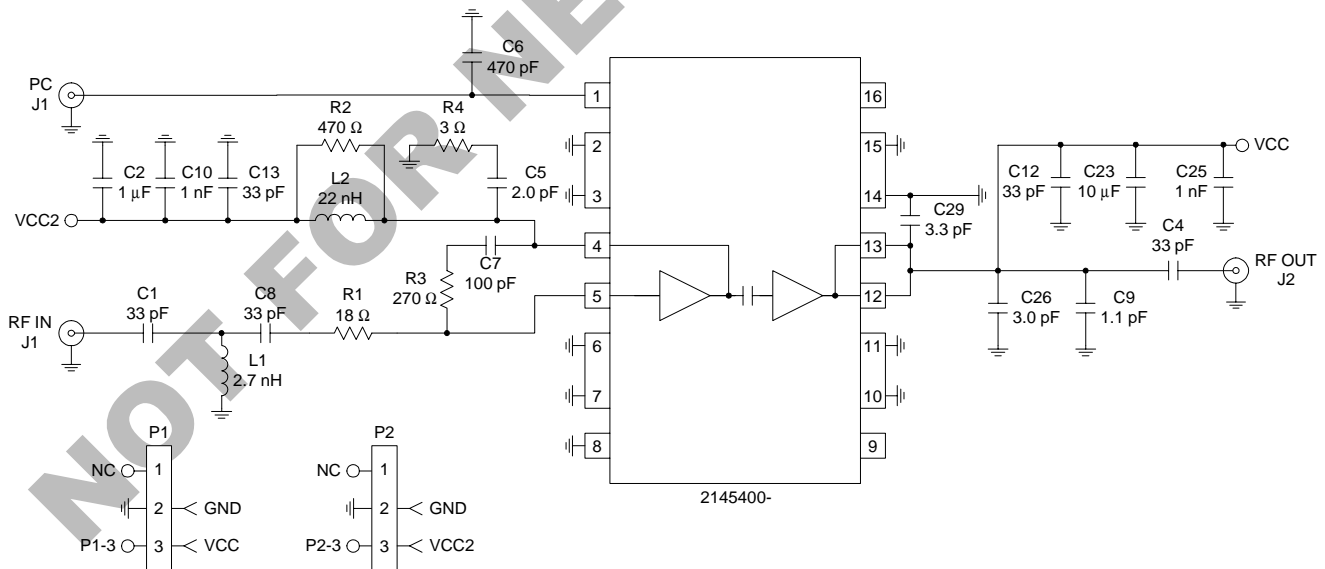
Application Schematic DCS 1800

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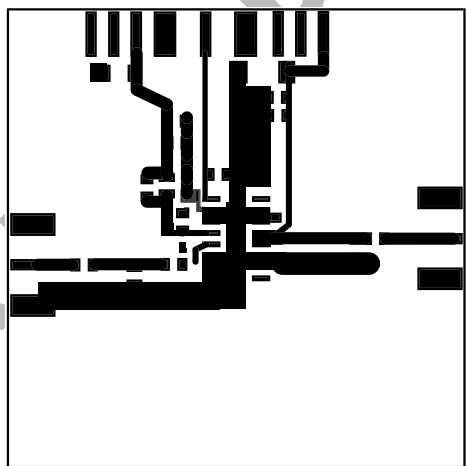
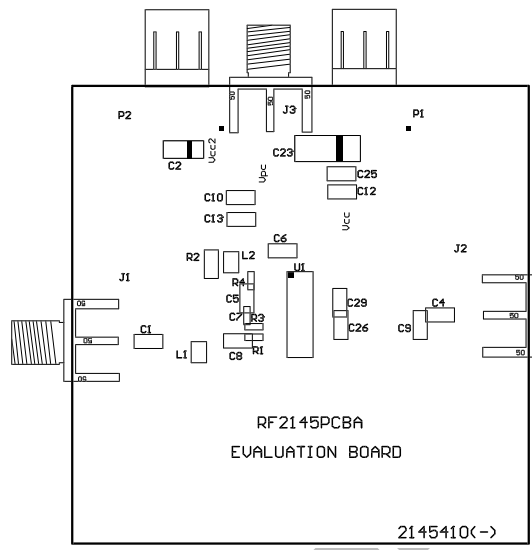
POWER AMPLIFIERS



Evaluation Board Schematic (Download Bill of Materials from www.rfmd.com.)



Evaluation Board Layout
2" x 2"



NOT FOR NEW DESIGNS